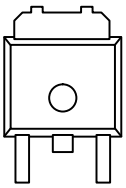
SUD15N06-90L

N-Channel
60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
60	0.065 @ V_{GS} = 10 V	15
	0.090 @ V_{GS} = 4.5 V	14

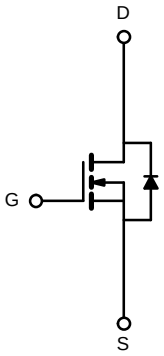
TO-252



Top View

Drain Connected to Tab

Order Number:
SUD15N06-90L



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (T_J = 175°C)	T_C = 25°C	I_D	15	A
	T_C = 100°C		12	
Pulsed Drain Current		I_{DM}	30	
Continuous Source Current (Diode Conduction)		I_S	15	
Avalanche Current		I_{AR}	15	
Repetitive Avalanche Energy (Duty Cycle ≤ 1%)	L = 0.1 mH	E_{AR}	11	mJ
Maximum Power Dissipation	T_C = 25°C	P_D	37	W
	T_A = 25°C		2[a]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 175	°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Free Air, FR4 Board Mount[a]	R_{thJA}	60	70	°C/W
Junction-to-Case	R_{thJC}	3.7	4.0	

Notes:
a. 1.36 x 2.1 surface mounted on 1” x 1” FR4 Board.

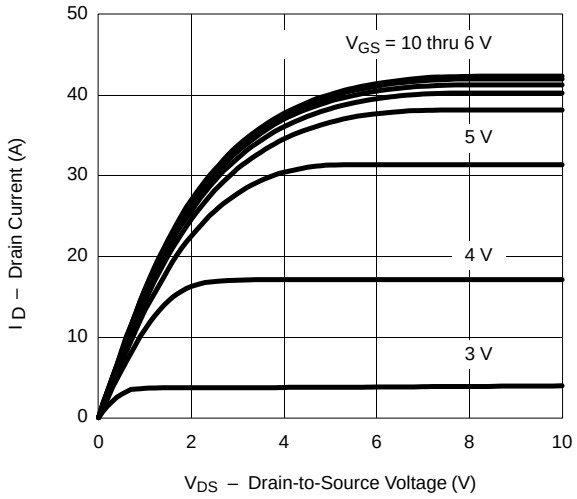
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ[a]	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	1.0	2.0	3.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			1	μA
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 125°C			50	
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 175°C			150	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	15			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 10 A		0.050	0.065	Ω
		V_{GS} = 10 V, I_D = 10 A, T_J = 125°C			0.12	
		V_{GS} = 10 V, I_D = 10 A, T_J = 175°C			0.15	
		V_{GS} = 4.5 V, I_D = 5 A		0.065	0.090	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 10 A		11		S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		524		pF
Output Capacitance	C_{oss}			98		
Reverse Transfer Capacitance	C_{rss}			28		
Total Gate Charge[c]	Q_g	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 15 A		12	20	nC
Gate-Source Charge[c]	Q_{gs}			2		
Gate-Drain Charge[c]	Q_{gd}			3.5		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 2 Ω I_D ≅ 15 A, V_{GEN} = 10 V, R_G = 2.5 Ω		7	20	ns
Rise Time[c]	t_r			8	25	
Turn-Off Delay Time[c]	$t_{d(off)}$			15	40	
Fall Time[c]	t_f			7	20	
Source-Drain Diode Ratings and Characteristics (T_C = 25°C)						
Pulsed Current	I_{SM}				30	A
Diode Forward Voltage	V_{SD}	I_F = 15 A, V_{GS} = 0 V		0.9	1.2	V
Reverse Recovery Time	t_{rr}	I_F = 15 A, di/dt = 100 A/μs		29	60	ns

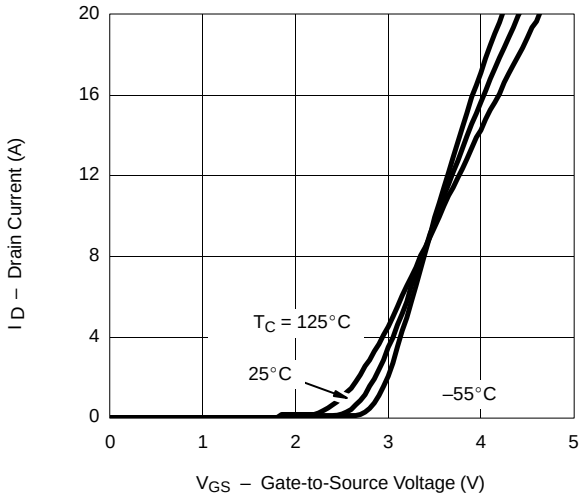
Notes:
a. For design aid only; not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

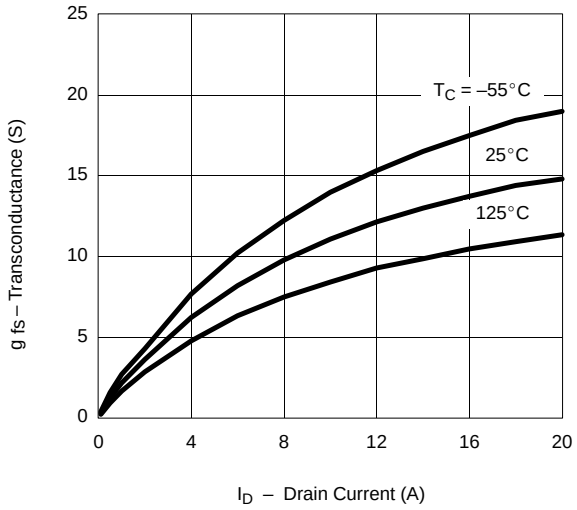
Output Characteristics



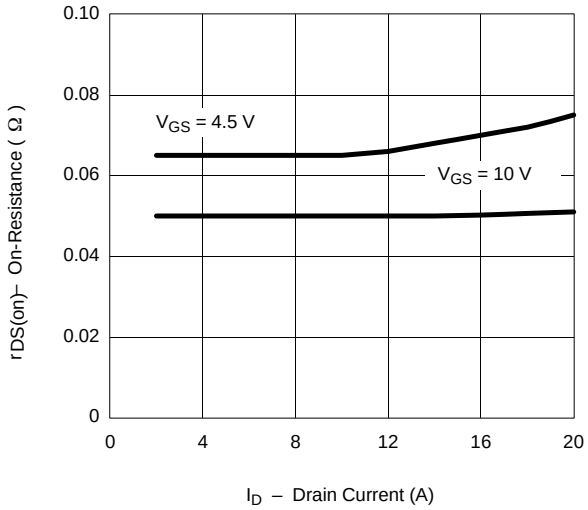
Transfer Characteristics



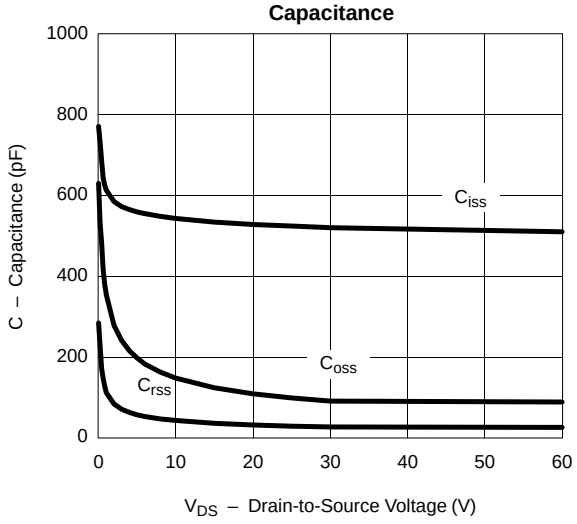
Transconductance



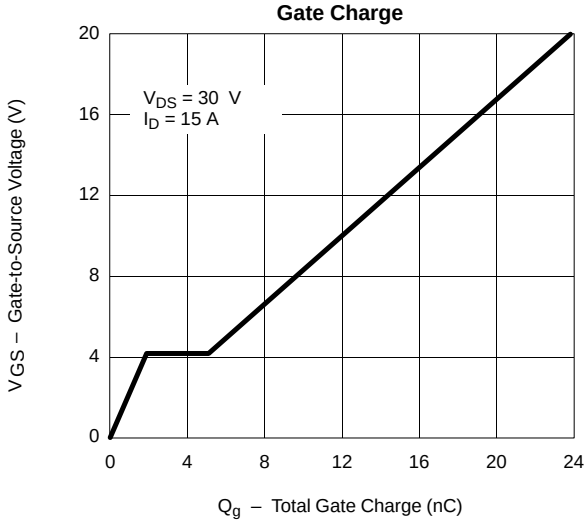
On-Resistance vs. Drain Current



Capacitance

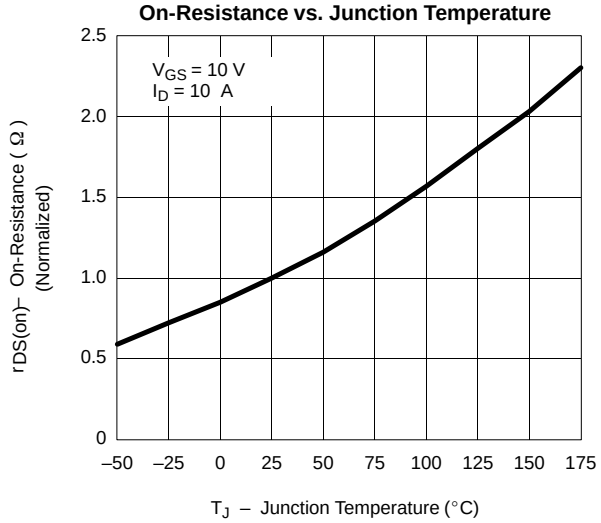


Gate Charge

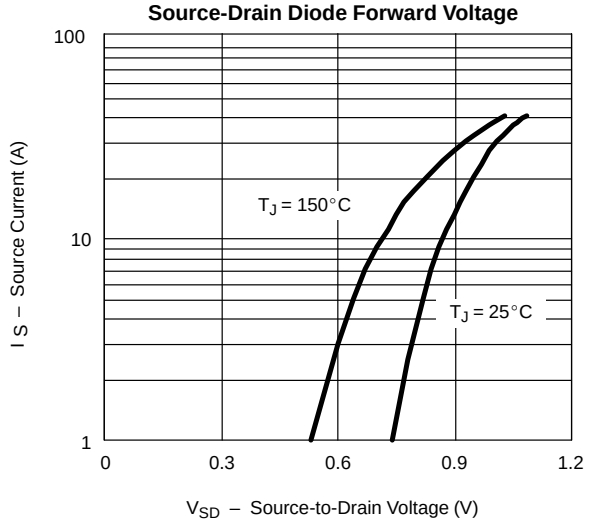


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

On-Resistance vs. Junction Temperature

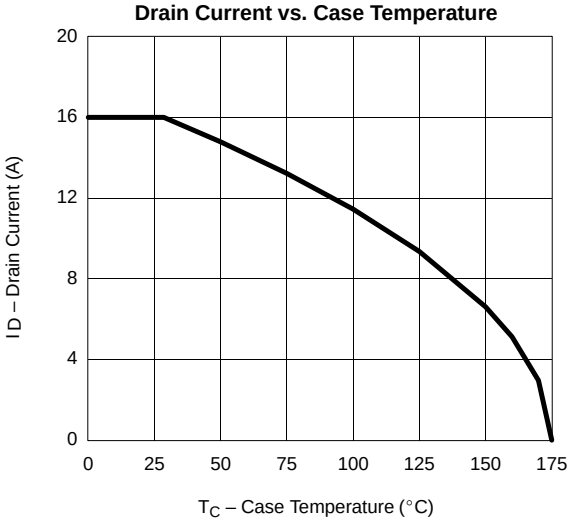


Source-Drain Diode Forward Voltage

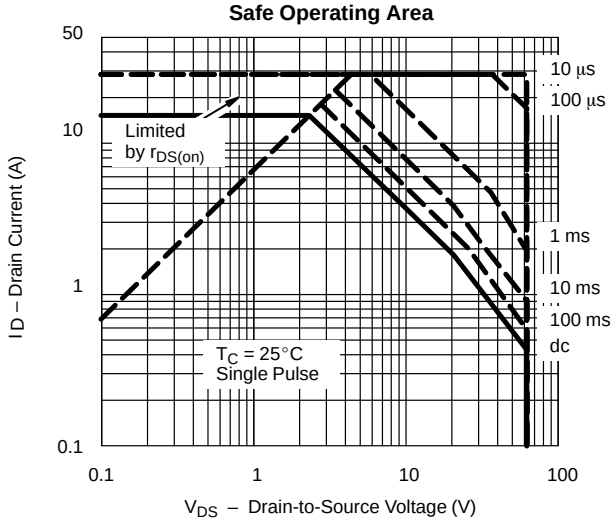


THERMAL RATINGS

Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case